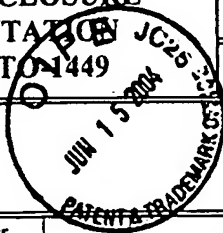


| | | |
|--|--------------------------------------|-----------------------|
| INFORMATION DISCLOSURE CITATION PTO 449 | Atty. Docket No. 042071 | Serial No. 10/768,090 |
| | Applicant(s): Chikako YOSHIDA et al. | |
| | Filing Date: February 2, 2004 | Group Art Unit: 2811 |



U.S. PATENT DOCUMENTS

| Examiner Initial | Document No. | Name | Date | Class | Subclass | Filing Date (If appropriate) |
|------------------|--------------|------|------|-------|----------|------------------------------|
| | | | | | | |
| | | | | | | |
| | | | | | | |
| | | | | | | |

FOREIGN PATENT DOCUMENTS

| Examiner Initial | Document No. | Date | Country | Translation (Yes or No) |
|------------------|-----------------|---------|---------|-------------------------|
| TTN | WO 03/014830 A1 | 2/20/03 | WIPO | |
| | 11307549 A | 11/5/99 | Japan | Yes |
| | 10073927 | 3/17/98 | Japan | Yes |
| | 08115923 A | 5/7/96 | Japan | Yes |
| | 07153666 A | 6/16/95 | Japan | Yes |
| | 2002-033320 A | 1/31/02 | Japan | Yes |
| TTN | 2001-267566 | 9/28/01 | Japan | Yes |
| | | | | |
| | | | | |
| | | | | |

OTHER DOCUMENTS

| | | |
|----------|--------------------|---|
| | | D.C. Gilmer et al., "Compatibility of Polycrystalline Silicon Gate Deposition with HfO ₂ and Al ₂ O ₃ /HfO ₂ gate dielectrics", Appl. Phys. Lett., Vol. 81, No. 7, pp. 1288-1290. |
| Examiner | <i>[Signature]</i> | Date Considered 04/05/2005 |